

V_{DRM}	=	1800 V
$I_{T(AV)M}$	=	4390 A
$I_{T(RMS)}$	=	6890 A
I_{TSM}	=	$64 \cdot 10^3$ A
V_{T0}	=	0.85 V
r_T	=	0.07 m Ω

Phase Control Thyristor

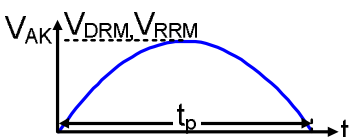
5STP 42L1800

Doc. No. 5SYA1075-02 Apr. 14

- Patented free-floating silicon technology
- Low on-state and switching losses
- Designed for traction, energy and industrial applications
- Optimum power handling capability
- Interdigitated amplifying gate

Blocking

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	5STP 42L1800	Unit
Max repetitive peak forward and reverse blocking voltage	V_{DRM}, V_{RRM}	$f = 50$ Hz, $t_p = 10$ ms, $T_{vj} = 5 \dots 125$ °C, Note 1 	1800	V
Critical rate of rise of commutating voltage	dv/dt_{crit}	Exp. to $0.67 \cdot V_{DRM}$, $T_{vj} = 125$ °C	1000	V/ μ s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward leakage current	I_{DRM}	V_{DRM} , $T_{vj} = 125$ °C			300	mA
Reverse leakage current	I_{RRM}	V_{RRM} , $T_{vj} = 125$ °C			300	mA

Note 1: Voltage de-rating factor of 0.11% per °C is applicable for T_{vj} below +5 °C.

Mechanical data

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_M		63	70	84	kN
Acceleration	a	Device unclamped			50	m/s ²
Acceleration	a	Device clamped			100	m/s ²

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m				1.45	kg
Housing thickness	H	$F_M = 70$ kN, $T_a = 25$ °C	25.8		26.4	mm
Surface creepage distance	D_s		36			mm
Air strike distance	D_a		15			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

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On-state

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Average on-state current	$I_{T(AV)M}$	Half sine wave, $T_c = 70\text{ °C}$			4390	A
RMS on-state current	$I_{T(RMS)}$				6890	A
Peak non-repetitive surge current	I_{TSM}	$t_p = 10\text{ ms}$, $T_{vj} = 125\text{ °C}$, sine half wave, $V_D = V_R = 0\text{ V}$, after surge			$64 \cdot 10^3$	A
Limiting load integral	I^2t				$20.48 \cdot 10^6$	A ² s
Peak non-repetitive surge current	I_{TSM}	$t_p = 10\text{ ms}$, $T_{vj} = 125\text{ °C}$, sine half wave, $V_R = 0.6 \cdot V_{RRM}$, after surge			$40 \cdot 10^3$	A
Limiting load integral	I^2t				$8 \cdot 10^6$	A ² s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_T	$I_T = 3000\text{ A}$, $T_{vj} = 125\text{ °C}$			1.05	V
Threshold voltage	$V_{(T0)}$	$I_T = 2500\text{ A} - 7500\text{ A}$, $T_{vj} = 125\text{ °C}$			0.85	V
Slope resistance	r_T				0.07	mΩ
Holding current	I_H	$T_{vj} = 25\text{ °C}$			150	mA
		$T_{vj} = 125\text{ °C}$			100	mA
Latching current	I_L	$T_{vj} = 25\text{ °C}$			800	mA
		$T_{vj} = 125\text{ °C}$			500	mA

Switching

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Critical rate of rise of on-state current	di/dt_{crit}	$T_{vj} = 125\text{ °C}$, $I_{TRM} = 3000\text{ A}$, $V_D \leq 0.67 \cdot V_{DRM}$, $I_{FG} = 2\text{ A}$, $t_r = 0.5\text{ }\mu\text{s}$			250	A/ μs
		Cont. $f = 50\text{ Hz}$			1000	A/ μs
Circuit-commutated turn-off time	t_q	$T_{vj} = 125\text{ °C}$, $I_{TRM} = 2000\text{ A}$, $V_R = 200\text{ V}$, $di_T/dt = -1.5\text{ A}/\mu\text{s}$, $V_D \leq 0.67 \cdot V_{DRM}$, $dV_D/dt = 20\text{ V}/\mu\text{s}$			250	μs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse recovery charge	Q_{rr}	$T_{vj} = 125\text{ °C}$, $I_{TRM} = 2000\text{ A}$, $V_R = 200\text{ V}$, $di_T/dt = -1.5\text{ A}/\mu\text{s}$	800		1900	μAs
Reverse recovery current	I_{RM}				95	A
Gate turn-on delay time	t_{gd}	$T_{vj} = 25\text{ °C}$, $V_D = 0.4 \cdot V_{RM}$, $I_{FG} = 2\text{ A}$, $t_r = 0.5\text{ }\mu\text{s}$			3	μs

Triggering

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Peak forward gate voltage	V _{FGM}				12	V
Peak forward gate current	I _{FGM}				10	A
Peak reverse gate voltage	V _{RGM}				10	V
Average gate power loss	P _{G(AV)}		see Fig. 7			W

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Gate-trigger voltage	V _{GT}	T _{vj} = 25 °C			2.6	V
Gate-trigger current	I _{GT}	T _{vj} = 25 °C			400	mA
Gate non-trigger voltage	V _{GD}	V _D = 0.4·V _{DRM} , T _{vjmax} = 125 °C			0.3	V
Gate non-trigger current	I _{GD}	V _D = 0.4·V _{DRM} , T _{vjmax} = 125 °C			10	mA

Thermal

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	T _{vj}				125	°C
Storage temperature range	T _{stg}		-40		140	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case,	R _{th(j-c)}	Double-side cooled F _m = 63... 84 kN			7	K/kW
	R _{th(j-c)A}	Anode-side cooled F _m = 63... 84 kN			14	K/kW
	R _{th(j-c)C}	Cathode-side cooled F _m = 63... 84 kN			14	K/kW
Thermal resistance case to heatsink,	R _{th(c-h)}	Double-side cooled F _m = 63... 84 kN			1.5	K/kW
	R _{th(c-h)}	Single-side cooled F _m = 63... 84 kN			3	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

i	1	2	3	4
R _i (K/kW)	4.700	0.853	1.070	0.490
τ _i (s)	0.4787	0.0824	0.0104	0.0041

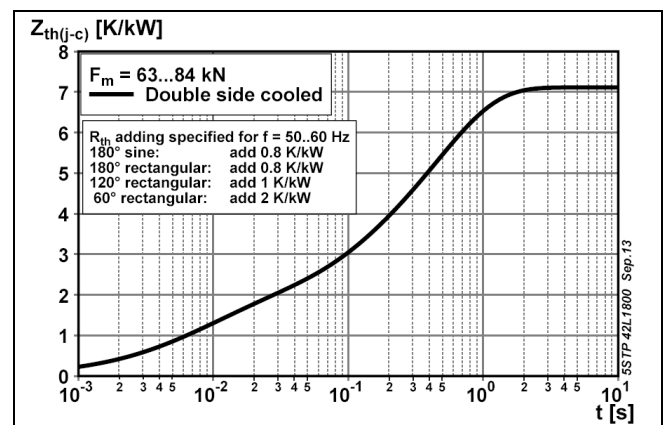


Fig. 1 Transient thermal impedance (junction-to-case) vs. time

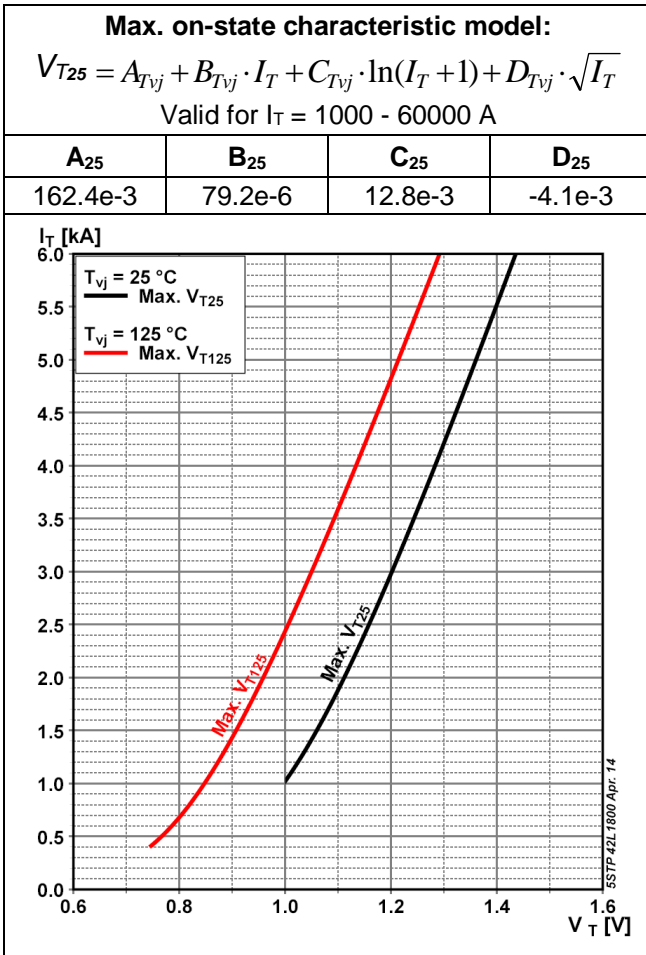


Fig. 2 On-state voltage characteristics

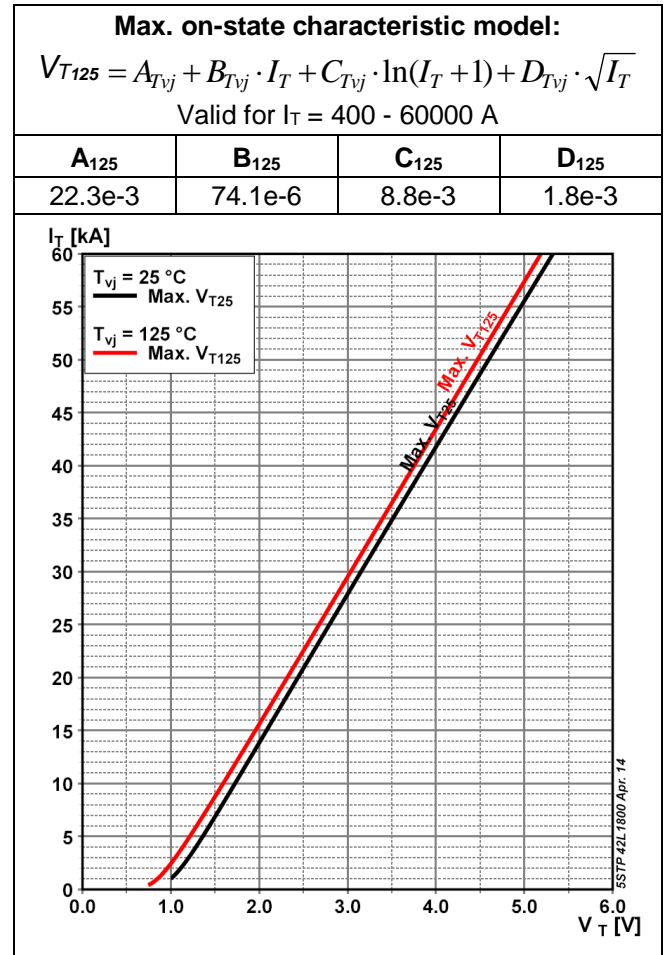


Fig. 3 On-state voltage characteristics

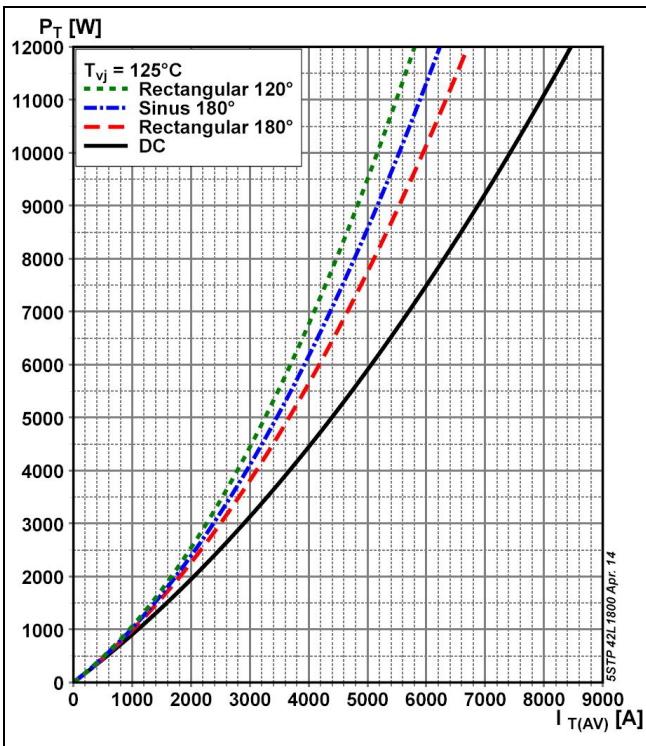


Fig. 4 On-state power dissipation vs. mean on-state current, turn-on losses excluded

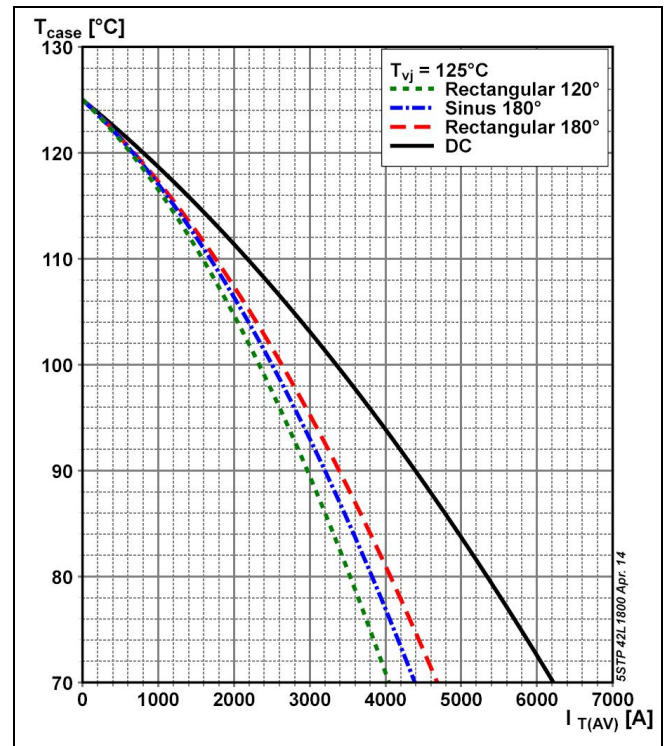


Fig. 5 Max. permissible case temperature vs. mean on-state current, switching losses ignored

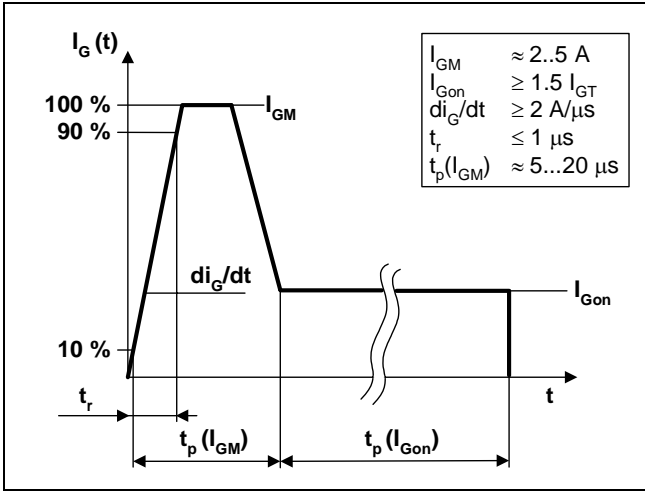


Fig. 6 Recommended gate current waveform

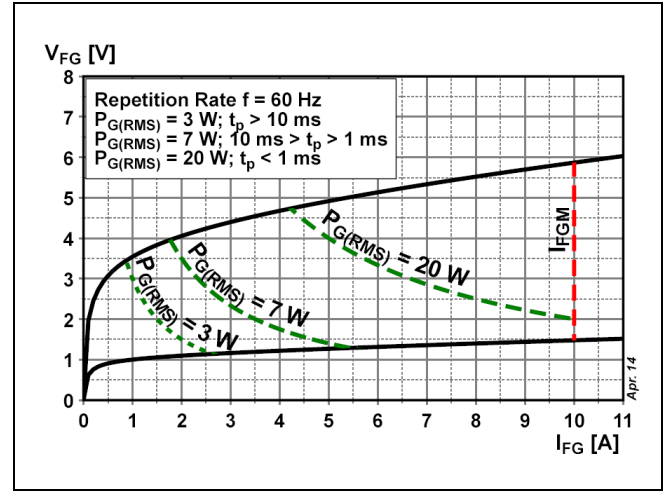


Fig. 7 Max. peak gate power loss

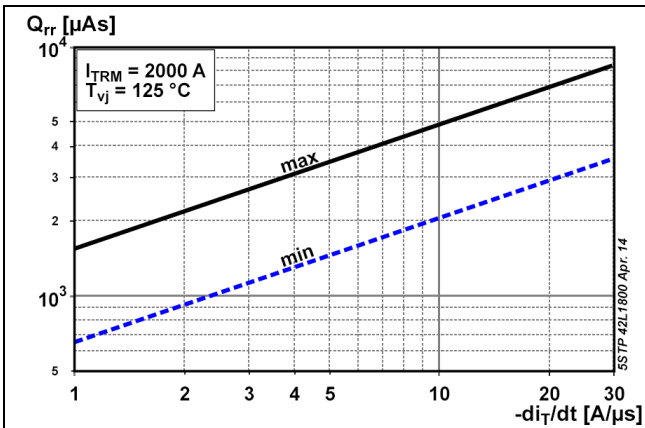


Fig. 8 Reverse recovery charge vs. decay rate of on-state current

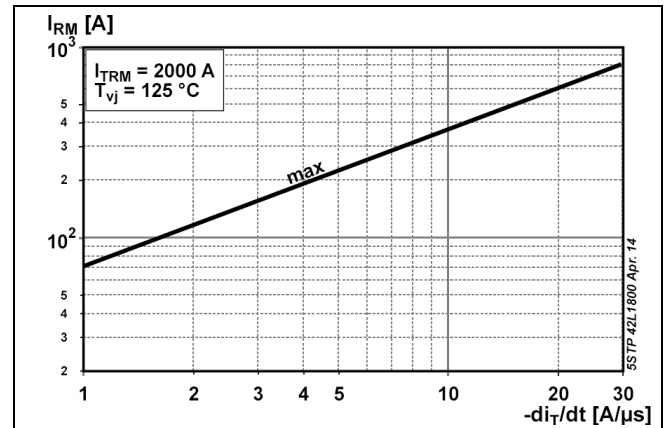


Fig. 9 Peak reverse recovery current vs. decay rate of on-state current

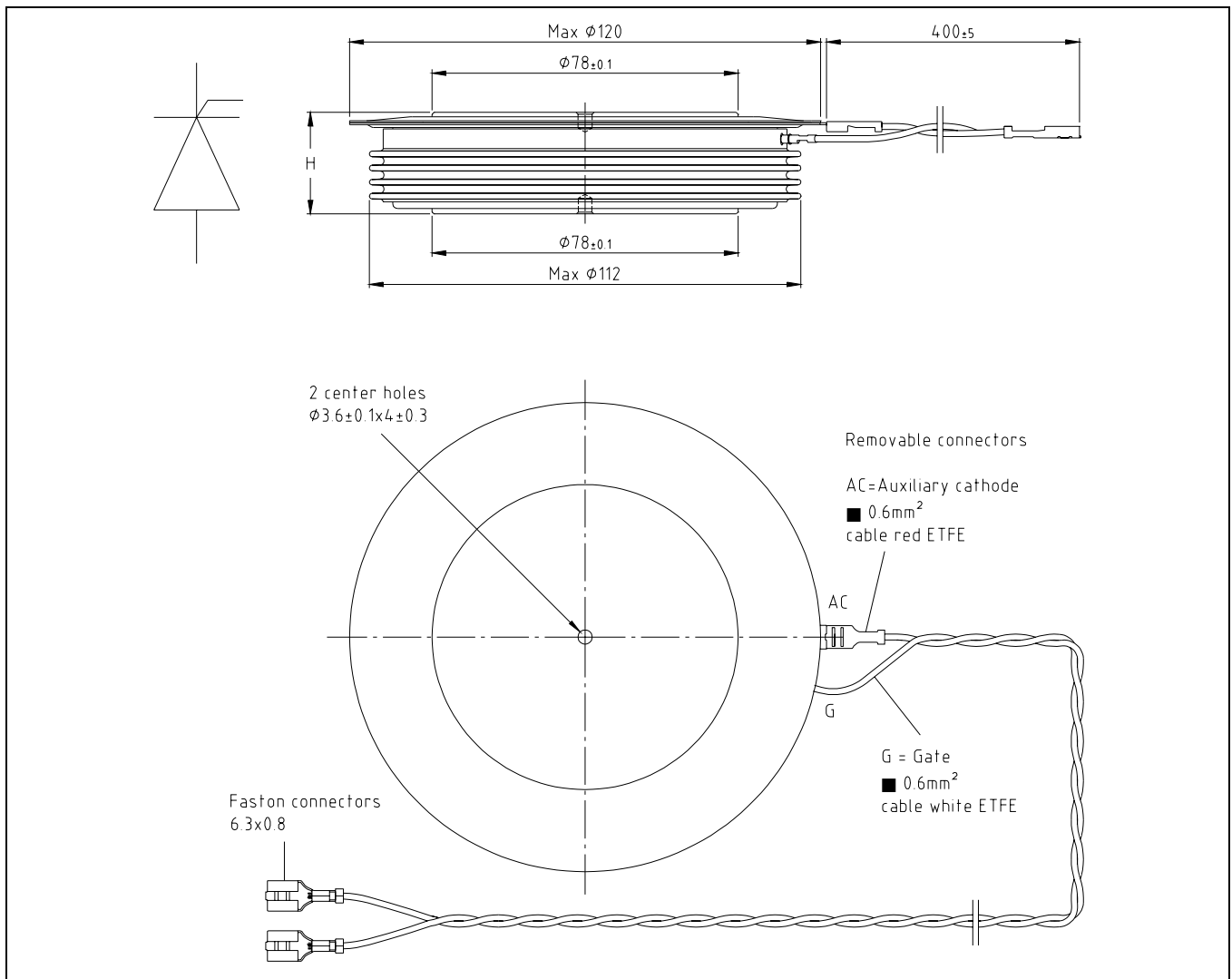


Fig. 10 Device Outline Drawing

Related documents:

5SYA 2020	Design of RC-Snubber for Phase Control Applications
5SYA 2049	Voltage definitions for phase control thyristors and diodes
5SYA 2051	Voltage ratings of high power semiconductors
5SYA 2034	Gate-Drive Recommendations for PCT's
5SYA 2036	Recommendations regarding mechanical clamping of Press Pack High Power Semiconductors
5SYA 2102	Surge currents for Phase Control Thyristors
5SZK 9104	Specification of environmental class for pressure contact diodes, PCTs and GTO, STORAGE
5SZK 9105	Specification of environmental class for pressure contact diodes, PCTs and GTO, TRANSPORTATION
5SZK 9115	Specification of environmental class for presspack Diodes, PCTs and GTOs, OPERATION (Industry)
5SZK 9116	Specification of environmental class for presspack Diodes, PCTs and GTOs, OPERATION (Traction)

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